

Delayed switching applied to memristor neural networks

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Magnetic flux and electric charge are linked in a memristor. We reported recently that a memristor has a peculiar effect in which the switching takes place with a time delay because a memristor possesses a certain inertia. This effect was named the “delayed switching effect.” In this work, we elaborate on the importance of delayed switching in a brain-like computer using memristor neural networks. The effect is used to control the switching of a memristor synapse between two neurons that fire together (the Hebbian rule). A theoretical formula is found, and the design is verified by a simulation. We have also built an experimental setup consisting of electronic memristive synapses and electronic neurons. © 2012 American Institute of Physics. [doi:10.1063/1.3672409]

I. INTRODUCTION

Since the first computer was built, scientists have been fascinated with the idea of a computer that works similarly as the human brain. However, all previous efforts at building brain-like computers failed because it took about the same silicon area to emulate a CMOS synapse as was needed to emulate a neuron. In a typical human brain, there are 10^{11} neurons and 10^{14} synapses (on average, each neuron is connected to other neurons through about 20 000 synapses). Any realistic implementation of a synapse should ideally be at least four orders of magnitude smaller than that required to build a neuron. Although the implementation of a neuron is relatively easier, an electronic synapse is not so straightforward to make for the above-stated reason.

The invention of the memristor¹ provides a new way to implement synapses. A memristor is a simple 2-terminal element, which means a vast number of memristors could be integrated together with other CMOS elements in a single chip. A $\text{LaAlO}_3/\text{SrTiO}_3$ junction presents a uni-polar pinched hysteresis loop and also provides the potential for a memristor to be scaled down to half a nanometer.² Memristors are passive and non-volatile and consume much less power.

Naturally, the freezing memory property by which a memristor stores resistance value makes memristors suitable for use as synapses. As shown in Fig. 1(b), the switching from high resistance (R_{off}) to low resistance (R_{on}) takes place with a time delay T_d after the application of an input voltage. In a memristor neural network, a square-wave signal is equivalent, in terms of switching a memristor synapse, to a sequence of spikes with the same net area as the observation region bounded by the graph of the signal and the time axis (Fig. 1(c)). This is because charge is the time integral of current, and the mem-resistance is normally a function of charge.

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The resistance of a memristor depends on the complete past history of the current, i.e., the time integral of the current from $\tau = -\infty$ to $\tau = t$. As mentioned above, the current (voltage) is a sequence of spikes with a frequency f and a (equal) spike width T_w . Therefore,

$$q(t) = \int_{-\infty}^{+t} i(\tau) d\tau = \int_{-\infty}^{+t} \frac{V d\tau}{R} = \frac{V}{R} \cdot T_w \cdot f \cdot t. \quad (1)$$

At the transition where $t = T_{d1,2}$, we have $q(T_{d1,2}) = Q_{1,2}$ and $\phi(T_{d1,2}) = \Phi_{1,2}$. Therefore,

$$Q_{1,2} = \frac{V}{\phi_{1,2}} \cdot T_w \cdot f \cdot T_{d1,2}, \quad (2)$$

$$T_{d1,2} = \frac{\phi_{1,2}}{V \cdot T_w \cdot f}, \quad T_{d1} = \frac{\phi_1}{V \cdot T_w \cdot f}, \quad T_{d2} = \frac{\phi_2}{V \cdot T_w \cdot f}. \quad (3)$$

Equation (3) clearly demonstrates that T_d decreases with an increased spike amplitude V , an increased spike width T_w , or an increased spike frequency f . If the input voltage is removed before the switching takes place, i.e., the width T of the input voltage pulse is smaller than $T_d \approx T_{d1} \approx T_{d2}$, the memristor remains unaltered. Therefore, in order to switch a memristor, T should be chosen in such a way that $T > T_d$.

II. DELAYED SWITCH IN MEMRISTOR NEURAL NETWORKS

As shown in Fig. 2, we consider a simplified neural network comprising three neurons (N1, N2, and N3) coupled by two memristive synapses (S1 and S2). This network can perform the Pavlovian experiment on conditioned reflex. The first input neuron (presumably located in the visual cortex) activates under a specific visual event, such as “sight of food,” and the second input neuron (presumably located in

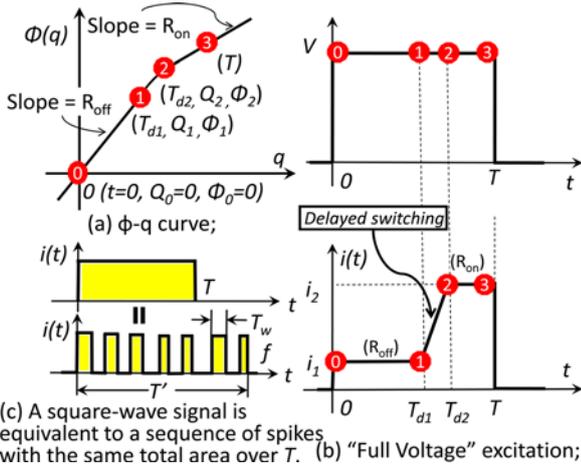


FIG. 1. (Color online) Memristor's delayed switching effect (Refs. 3 and 4): the switching from one resistance state to another due to an input voltage pulse takes place with a time delay. The effect also applies to a sequence of spikes, well used in neural networks.

73 the auditory cortex) activates under an external auditory
 74 event, such as “sound of bell.” Depending on previous training,
 75 each of these events can trigger “salivation” (firing of the
 76 third output neuron). If, at a certain moment in time, only the
 77 sight of food leads to salivation, and subsequently the circuit is
 78 subjected to both input events, then, after a sufficient number
 79 of simultaneous input events, the circuit starts associating the
 80 sound of a bell with the sight of food, and eventually it begins
 81 to salivate upon the activation of the sound only. This process
 82 of learning is a realization of the famous Hebbian rule.⁵

84 A biological neuron behaves like an analog-to-digital converter.
 85 When a neuron receives a receptor potential exceeding a threshold
 86 value, it starts emitting both forward (along the output terminal
 87 of the neuron) and backward (along the input of the neuron) action
 88 spikes; the amplitude of these spikes is constant, but their
 89 frequency depends on the stimulus strength.

90 A biological synapse is a connection that permits a neuron to
 91 pass an electrical signal to another neuron. Our memristor synapse
 92 is modeled in Fig. 1(a). As shown in Fig. 2, the synapse S1
 93 receives a voltage determined by the output of the neuron N1 at
 94 its front (forward-propagating spikes) and the input of another
 95 neuron N3 at its back (back-

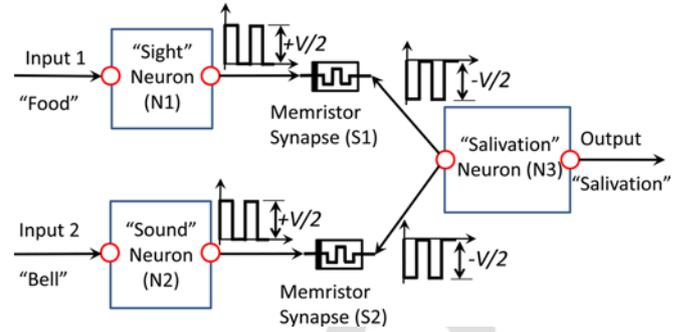


FIG. 2. (Color online) A neural network using memristors as synapses. When a neuron fires, it starts emitting a forward spike, $+V/2$, and a backward spike, $-V/2$. The strengths of memristor synapses can be modified when these two spikes overlap.

propagating spikes). If the pre-synaptic and post-synaptic
 spikes overlap, a positive “half voltage” ($+v/2$) and a negative
 “half voltage” ($-v/2$) generate a “full voltage” drop (v)
 across the synapse.

The simulation results are shown in Fig. 3. The width of
 each pulse (spike) is set at 4 time units, and the memristor
 synapse S2 remains unaltered (still disconnected). The simulation
 period is 6600 time units.

In the “probing” phase (“food” only or “bell” only in
 Fig. 3), the salivation neuron fires only when a stimulus
 signal is applied to the sight neuron, as S1 is connected and
 S2 is disconnected.

In the “learning” phase (Fig. 3), stimulus voltages are
 applied simultaneously to both input neurons (“sight” and
 “sound”), thus generating a sequence of spikes. The spikes
 from different neurons are uncorrelated, but sometimes they
 do overlap, owing to a random component in the spike
 separation. During this phase, in some moments of time,
 back-propagating spikes from the salivation neuron (due to
 excitation from the sight neuron) overlap with forward
 propagating spikes from the sound neuron, causing a full
 voltage across the second memristor synapse S2. As this
 voltage exceeds the memristor threshold, S2 changes its
 state and switches into a low resistance state (connection).
 It is important to note that this change is possible when
 both stimuli are applied together (in other words, they
 correlate). As a result, an association between input stimuli
 develops, and the

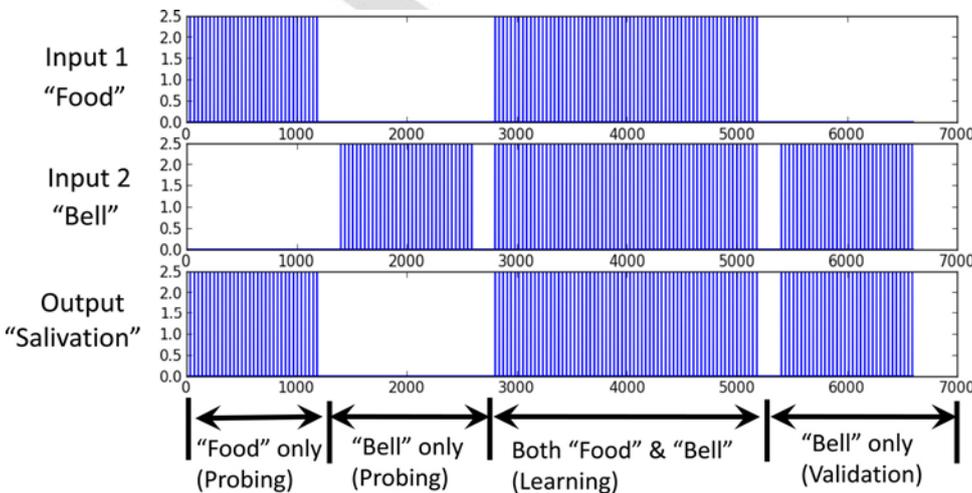


FIG. 3. (Color online) Simulation demonstration of the memristor neural network in Fig. 2.

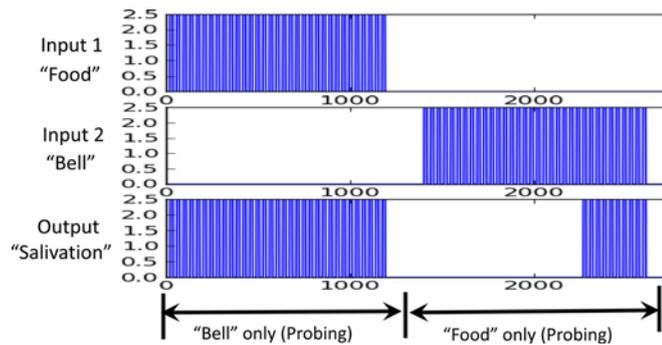


FIG. 4. (Color online) If each spike is too wide or the spike sequence is too long, the “salivation” will be triggered by mistake when only the “sound” neuron fires.

123 network “learns” to associate the sight neuron with the sound
124 neuron.

125 Our measurements during the second probing phase
126 (“validation” in Fig. 3) clearly demonstrate the developed
127 association. In this phase, any type of stimulus, whether
128 from the sight neuron or from the sound neuron, results in
129 the firing of the salivation neuron.

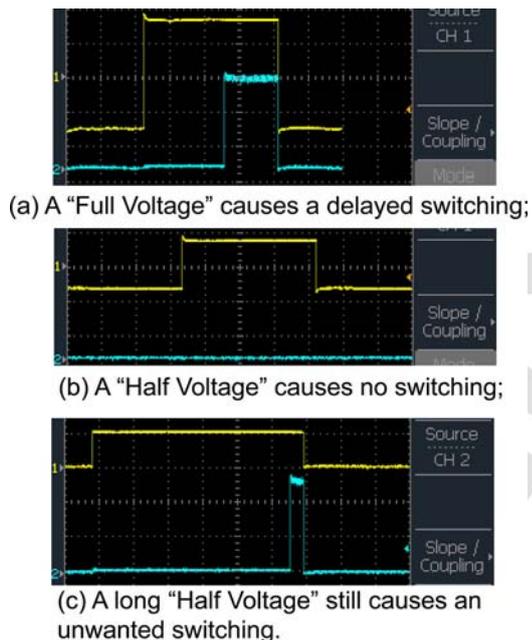


FIG. 5. (Color online) Measured waveform on an experimental setup consisting of electronic memristive synapses and electronic neurons. The “full voltage” is 5 V, and the “half voltage” is 2.5 V.

If the width of each spike is increased to 16 time units 130
(with the same frequency), the integral (charge) rises quickly 131
and the memristor time delay (Eq. (3)) is overtaken; as a 132
result, S2 will change its state even under a half voltage 133
(only the sound neuron fires), as shown in Fig. 4. Obviously 134
this is a mis-operation in which the sound neuron is connected 135
with the salivation neuron by mistake, violating the 136
Hebbian rule (“neurons that fire together, wire together”). 137

III. CIRCUIT EXPERIMENTS 138

Based on Chua’s “circuit-model,”¹ we have built an ex- 139
perimental setup consisting of electronic memristive synap- 140
ses and electronic neurons.³⁻⁵ The electronic memristor 141
synapse can be tuned to represent the functions found in bio- 142
logical neural cells.⁵ 143

The waveforms are measured with a 16 to 25 Hz square- 144
wave input signal, a low resistance of 625 Ω , and a high 145
resistance of 10 k Ω . As shown in Fig. 5, the application of 146
the delayed switching in a neural network has been achieved. 147

IV. CONCLUSION 148

A memristor mimics the synapses between the neurons 149
in the brain in terms of being plastic according to the dynam- 150
ical history of the system. According to Eq. (3), the sequence 151
length, sequence frequency, and spike width need to be care- 152
fully controlled in such a way that the memristor synapse 153
time delay point is not be overtaken while only one neuron 154
fires. 155

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